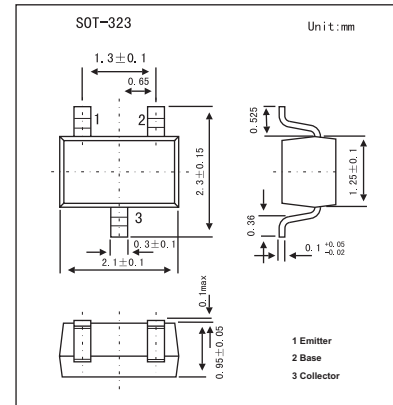


## Silicon PNP Epitaxial Planar Type

## 2SB1219

## ■ Features

- Large collector current  $I_c$ .

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-30	V
Collector-emitter voltage	$V_{CEO}$	-25	V
Emitter-base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-1	A
Collector current	$I_c$	-500	mA
Collector power dissipation	$P_c$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	$V_{CBO}$	$I_c = -10 \mu\text{A}$ , $I_E = 0$	-30			V
Collector-emitter voltage	$V_{CEO}$	$I_c = -2 \text{ mA}$ , $I_B = 0$	-25			V
Emitter-base voltage	$V_{EBO}$	$I_E = -10 \mu\text{A}$ , $I_c = 0$	-5			V
Collector-base cutoff current	$I_{CBO}$	$V_{CB} = -20 \text{ V}$ , $I_E = 0$			-0.1	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}$ , $I_c = -150 \text{ mA}$	85		340	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -300 \text{ mA}$ , $I_B = -30 \text{ mA}$		-0.35	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -300 \text{ mA}$ , $I_B = -30 \text{ mA}$		-1.1	-1.5	
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}$ , $I_E = 50 \text{ mA}$ , $f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$		6	15	pF

■  $h_{FE}$  Classification

Marking	CQ	CR	CS	C
$h_{FE}$	85~170	120~240	170~340	85~340